

IN THE CLAIMS:

Please amend the claims as follows:

Sub 1
B1
4. (Amended) The method of claim 3, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B2
14. (Amended) The method of claim 13, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B3
16. (Amended) The method of claim 11, wherein said capped shallow trench isolation structure includes ledges which extend a [predetermined] distance over said upper surface of said semiconductor substrate adjacent said opposing trench edges.

B4
27. (Amended) The method of claim 26, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B5
35. (Amended) The method of claim 34, wherein selectively etching said buffer film layer portion results in a portion of said buffer film layer remaining on said semiconductor substrate and extending a [predetermined] distance from said trench.

B6
37. (Amended) The method of claim 33, wherein said capped shallow trench isolation structure includes ledges which extend a [predetermined] distance over said upper surface of said semiconductor substrate adjacent said opposing trench edges.